

SOT-363 贴片塑封三极管
SOT-363 Plastic-Encapsulate Transistors

特征 Features

- 与 MMDT3904 配对; Complementary to MMDT3904
- 最大功率耗散 200mW; Power Dissipation of 200mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOT-363 封装 SOT-363 Small Outline Plastic Package
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter -Base Voltage	V _{EBO}	-5	V
Collector Current-Continuous	I _C	-200	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	625	°C/W

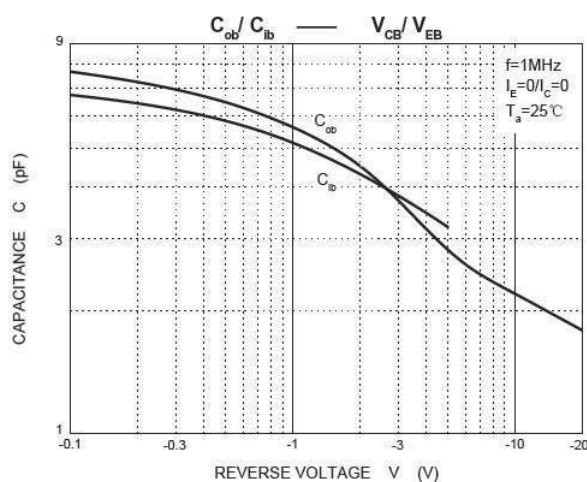
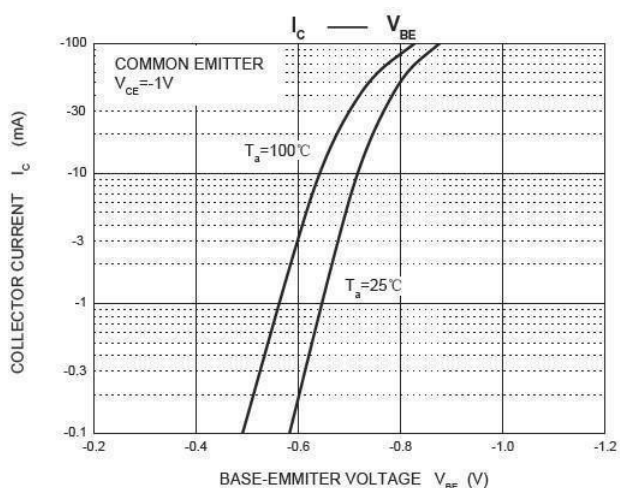
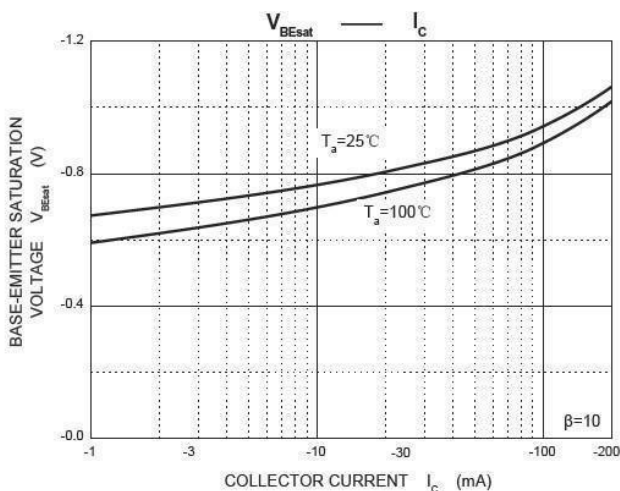
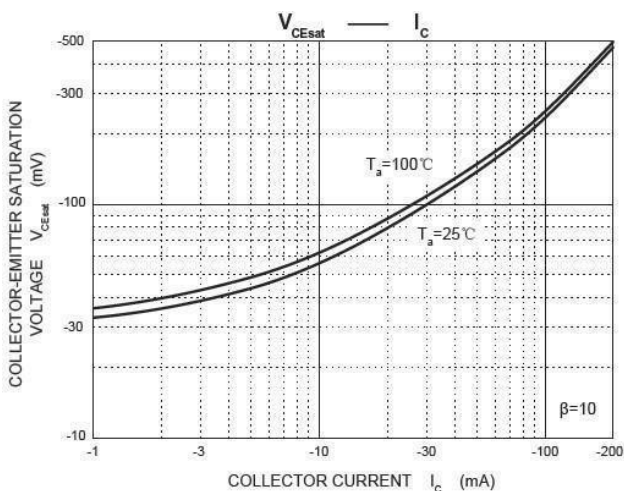
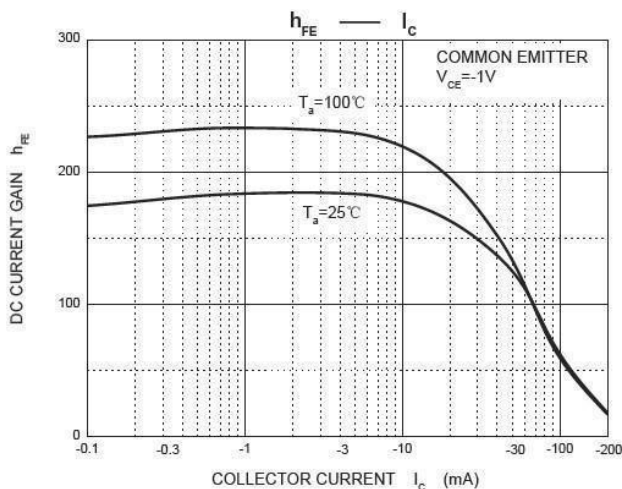
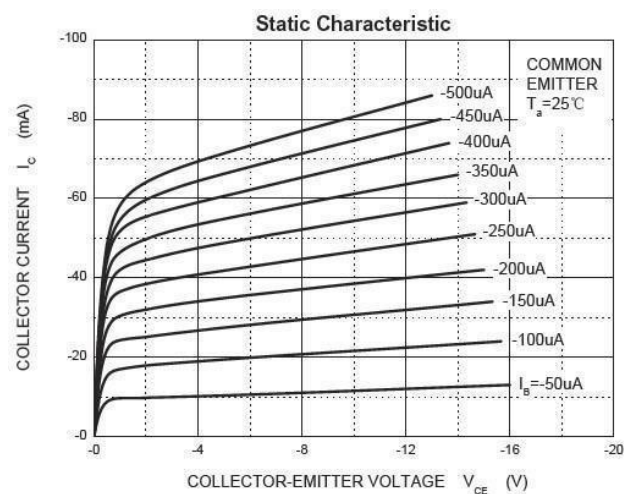
电特性 (TA = 25°C 除非另有规定)

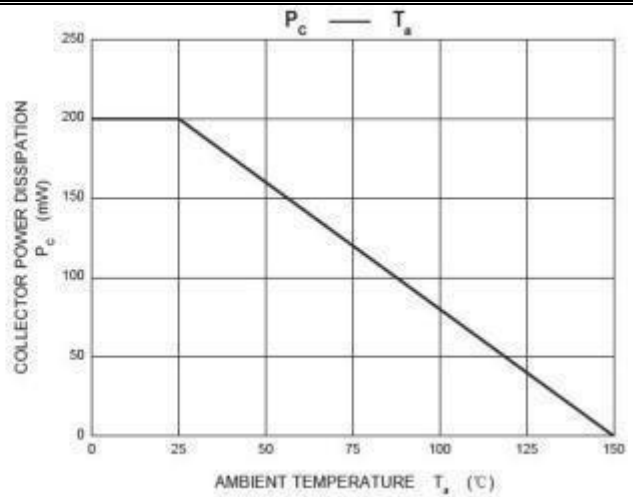
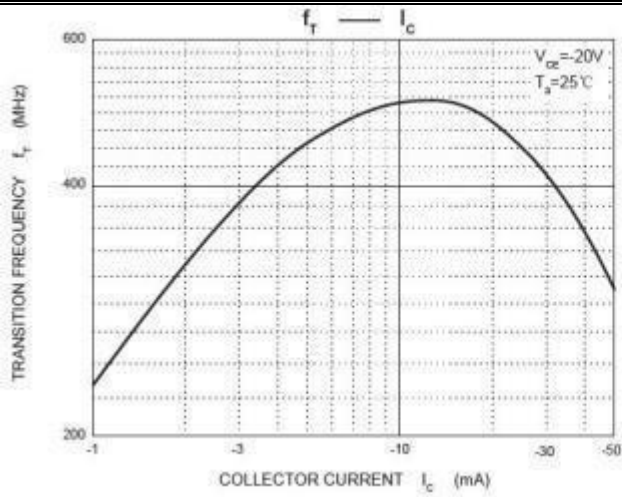
Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-50	nA
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{BE(off)} =-3V			-50	nA
DC current gain	h _{FE(1)}	V _{CE} =-1V, I _C =-0.1mA	60			
	h _{FE(2)}	V _{CE} =-1V, I _C =-1mA	80			
	h _{FE(3)}	V _{CE} =-1V, I _C =-10mA	100		300	
	h _{FE(4)}	V _{CE} =-1V, I _C =-50mA	60			
	h _{FE(5)}	V _{CE} =-1V, I _C =-100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =-10mA, I _B =-1mA			-0.25	V
	V _{CE(sat)2}	I _C =-50mA, I _B =-5mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _C =-10mA, I _B =-1mA	-0.65		-0.85	V
	V _{BE(sat)2}	I _C =-50mA, I _B =-5mA			-0.95	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	250			MHz
Delay time	t _d	V _{CC} =-3V, V _{BE(off)} =-0.5V			35	nS
Rise time	t _r	I _C =-10mA, I _{B1} =-I _{B2} = -1mA			35	nS
Storage time	t _s	V _{CC} =-3V, I _C =-			225	nS

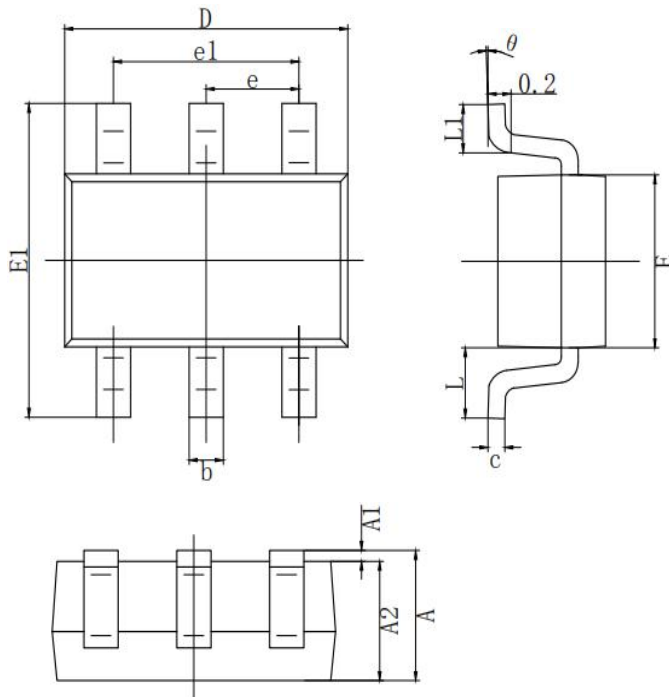
Fall time	t_f	10mA, $I_{B1}=-I_{B2}=-1mA$		75	nS
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典型特性曲线 Typical Characteristics Curve





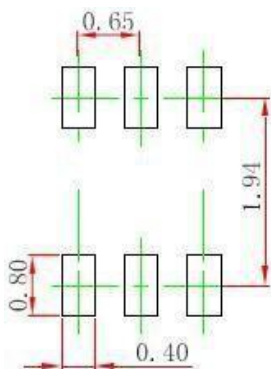
封装外形图 SOT-363 PACKAGE OUTLINE



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	0°	8°

焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-363. Electrode patterns for PCBs



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05mm$.
3. The pad layout is for reference purposes only.